

60A, 650V Ultrafast Diode with Dual Anode

Description

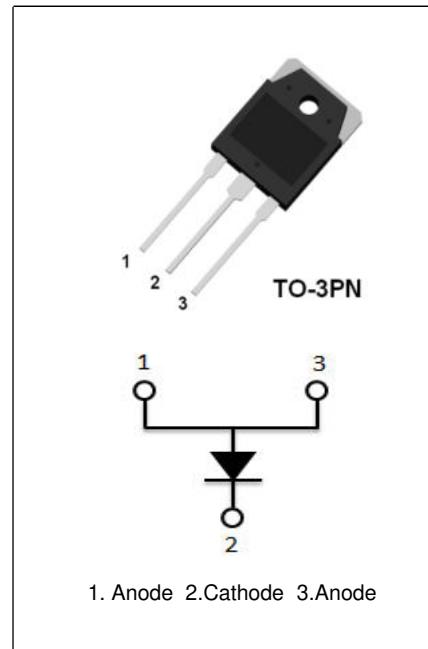
The AKF60U65NCN is an ultrafast diode with dual anode. It has lower forward voltage drop, more powerful avalanche energy, and better reliability. The series of device is specially suited for use in cutting machine and boost diode in PFC stages.

Features

- Ultrafast Soft Recovery: $t_{rr}=200\text{ns}$
- Typical Forward Voltage: $V_F=1.25\text{V} @ I_F=60\text{A}$
- Reverse Voltage: $V_{RRM}=650\text{V}$
- Avalanche Energy Rated

Applications

- Cutting Machine
- General Rectifier
- Boost diode in PFC stages
- FWD for Motor Application



Absolute Maximum Ratings

per diode at $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	650	V
V_{RWM}	Working Peak Reverse Voltage	650	V
V_R	DC Blocking Voltage	650	V
$I_{F(AV)}$	Average Rectified Forward Current	60	A
I_{FSM}	Non-repetitive Peak Surge Current	600	A
T_J	Operating Junction Temperature Range	-65~+150	°C
T_{STG}	Storage Temperature Range	-65~+150	°C

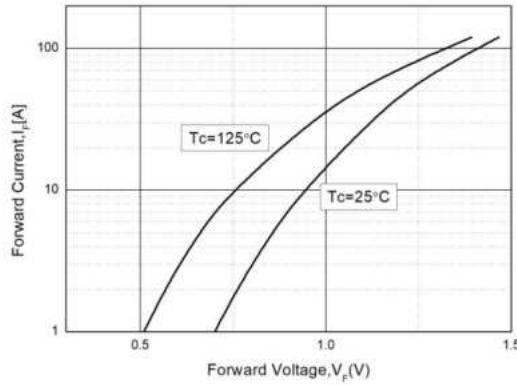
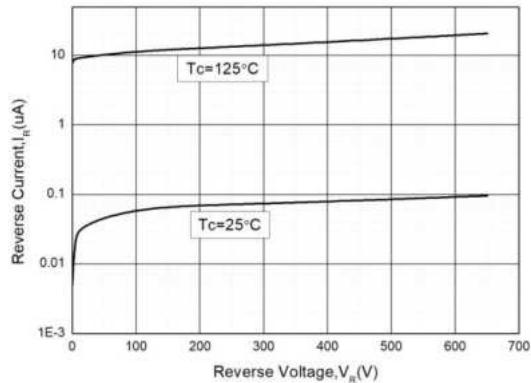
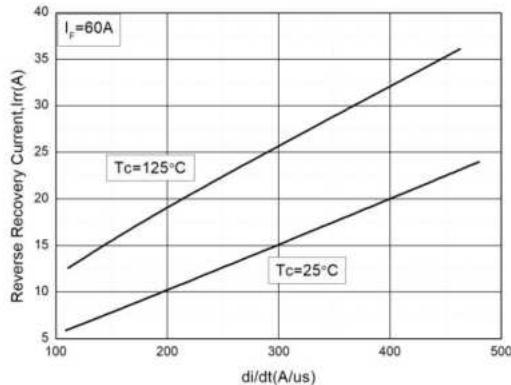
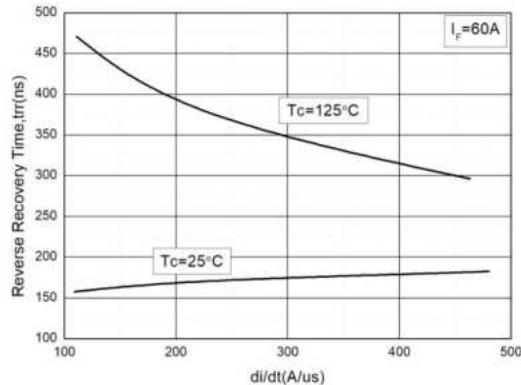
Thermal Characteristics

Symbol	Parameter	Ratings	Unit
$R_{th(J-C)}$	Thermal Resistance, Junction to case	0.45	°C/W

Electrical Characteristics per diode @ $T_c=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage Drop	$I_F=60\text{A}$	-	1.25	-	V
		$I_F=60\text{A}, T_c=125\text{ }^\circ\text{C}$	-	-	1.4	V
I_R	Reverse Leakage Current	$V_R=600\text{V}$	-	-	10	Ua
t_{rr}	Reverse Recovery Time	$I_F=60\text{A}, \text{di}/\text{dt}=-200\text{A}/\text{us}$	-	200	-	Ns
W_{AVL}	Avalanche Energy	$L=10\text{mH}$	100	-	-	mJ

Typical Performance Characteristics

 Fig. 1. Typical Characteristics: V_F vs. I_F

 Fig. 2. Typical Characteristics: V_R vs. I_R

 Fig. 3. Typical Reverse Recovery Time vs. di/dt

 Fig. 4. Typical Reverse Recovery Current vs. di/dt


Package Dimensions

TO-3PN

(Dimensions in Millimeters)

